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Docket No.: 8733.132.20-US

(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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TECHNOLOGY CENTER 2800

In re Patent Application of:
Joon-Young Yang

Application No.: 09/875,197

Group Art Unit: 2814

Filed: June 7, 2001

Examiner: S. Rao

For: METHOD OF FABRICATING A THIN FILM
TRANSISTOR

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was
enter w/KEE
3/7/2003

AMENDMENT UNDER 37 CFR 1.116

Box AF
Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action dated November 6, 2002, finally rejecting claims 21-34, 39 and 40, please amend the above-identified U.S. patent application as follows:

In the Claims

Please CANCEL Claims 21-34, 39 and 40 without prejudice.

Please ADD the following new claims:

41. (New) A method of fabricating a thin film transistor, comprising:

forming a gate insulating layer on an active layer;

forming a gate on the gate insulating layer;

forming an excited region in an exposed portion of the active layer by implanting hydrogen ions to the active layer by using the gate as a mask; and

DC:115800.1